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Vishay Semiconductors

# Thyristor High Voltage, Phase Control SCR, 50 A



PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub> 50 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V					
V <sub>TM</sub> (typ.)	1.1 V					
I <sub>GT</sub> (typ.)	35 mA					
TJ	-40 °C to +150 °C					
Package	TO-247AD 3L					
Circuit configuration	Single SCR					

#### **FEATURES**

 Designed and qualified according t JEDEC®-JESD 47



HALOGEN

Low I<sub>GT</sub> designed

• 150 °C maximum operating junction temperature

Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912

#### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

#### **DESCRIPTION**

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V					
V <sub>T</sub>	50 A, T <sub>J</sub> = 125 °C	1.1	V					
I <sub>T(AV)</sub>		50						
I <sub>RMS</sub>		79	Α					
I <sub>TSM</sub>		630						
dV/dt		500	V/µs					
T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C					

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-50TPS12AL-M3	1200	1300	10					



ABSOLUTE MAXIMUM RATINGS									
DADAMETED	SYMBOL TEST CONDITIONS		VAL	UNITS					
PARAMETER	STWIDUL	TEST CONDITIONS		TYP.	MAX.	UNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 112 °C, 180° conduction half sine wa	ive	=.	50				
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			-	79	А			
Peak, one-cycle non-repetitive surge current	l	10 ms sine pulse, rated V <sub>RRM</sub> applied		-	530				
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630				
I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	maximum	-	1405	A <sup>2</sup> s			
i-tior rusing	1-1	10 ms sine pulse, no voltage reapplied		-	1986				
$I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied, T <sub>J</sub> = 125 °C			19 850	A²√s			
Low level value of threshold voltage	V <sub>T(TO)1</sub>			-	0.89	V			
High level value of threshold voltage	V <sub>T(TO)2</sub>	T <sub>J</sub> = 125 °C		-	0.97	\ \ \			
Low level value of on-state slope resistance	r <sub>t1</sub>	1j=125 C		-	6.77	mΩ			
High level value of on-state slope resistance	r <sub>t2</sub>			-	6.32				
On atota valtaga	V	50 A, T <sub>J</sub> = 25 °C		1.2	1.32	V			
On-state voltage	V <sub>T</sub>	100 A, T <sub>J</sub> = 25 °C			1.6	V			
Rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C		-	150	A/µs			
Holding current	I <sub>H</sub>	Anada ayanlır. C.V. registiye laad. T. Of		-	300				
Latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		-	350	mA			
		T <sub>J</sub> = 25 °C		=	0.05	IIIA			
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C			10				
Rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum, linear to 80 % V <sub>DRM</sub> , R <sub>g</sub>	<sub>3</sub> -k = 100 Ω	-	500	V/µs			

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	P <sub>GM</sub>	10 ma aina nula	se, no voltage reapplied	-	10	W
Average gate power	P <sub>G(AV)</sub>	TO THS SITIE PUIS	se, no voltage reapplied	-	2.5	_ vv
Peak gate current	I <sub>GM</sub>			-	2.5	Α
Peak negative gate voltage	-V <sub>GM</sub>			-	10	
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	-	1.6	V
Required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		=	1.5	) v
		T <sub>J</sub> = 150 °C		=	1	
		T <sub>J</sub> = -40 °C		-	100	
Required DC gate to trigger	$I_{GT}$	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	35	60	mA
		T <sub>J</sub> = 150 °C	]	-	40	
DC gate voltage not to trigger	$V_{GD}$	T <sub>J</sub> = 150 °C, V <sub>DRM</sub> = rated value			0.15	V
DC gate current not to trigger	I <sub>GD</sub>	1J = 150 °C, VD	<sub>RM</sub> = rated value	-	2.5	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Turn-on time	t <sub>gt</sub>	$I_T = 50 \text{ A}, V_D = 50 \% V_{DRM}, I_{gt} = 300 \text{ mA}, T_J = 25 ^{\circ}\text{C}$	1.5	
Turn-off time	tq	$\begin{array}{l} I_T = 50 \text{ A, V}_D = 80 \text{ \% V}_{DRM},  dV/dt = 20 \text{ V/}\mu\text{s, t}_p = 200  \mu\text{s} \\ I_{gt} = 100 \text{ mA, dI/dt} = 10  A/\mu\text{s, V}_R = 100  \text{V, T}_J = 150  ^{\circ}\text{C} \end{array}$	92	μs



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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS			
Maximum junction and storage te	mperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40	150	°C			
Maximum thermal resistance, june	Maximum thermal resistance, junction to case			-	0.35				
Maximum thermal resistance, junction to ambient		$R_{thJA}$		-	40	°C/W			
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.2	-				
Mounting torque	minimum			6	(5)	kgf · cm			
Mounting torque	maximum			12 (10)		(lbf $\cdot$ in)			
Marking device			Case style Super TO-247AD 3L	;	50TPS12A	\L			

△R <sub>thJ-HS</sub> CONDUCTION PER JUNCTION											
DEVICE	SINE HALF-WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION					ION	LIMITO				
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12L-M3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

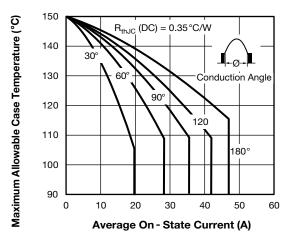
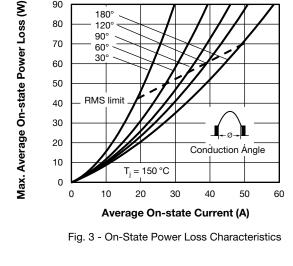


Fig. 1 - Current Rating Characteristics



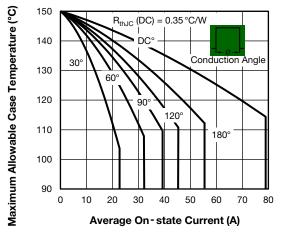


Fig. 2 - Current Rating Characteristics

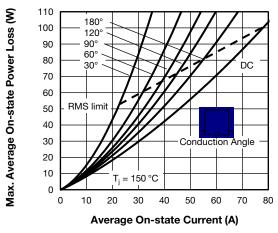


Fig. 4 - On-State Power Loss Characteristics

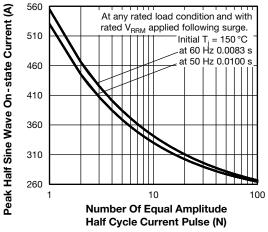


Fig. 5 - Maximum Non-Repetitive Surge Current

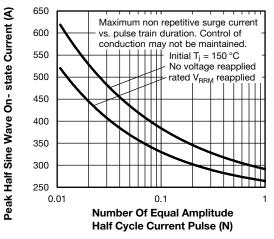


Fig. 6 - Maximum Non-Repetitive Surge Current

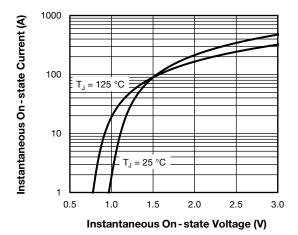


Fig. 7 - On-State Voltage Drop Characteristics

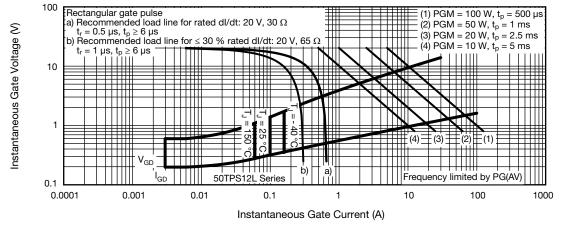


Fig. 8 - Gate Characteristics

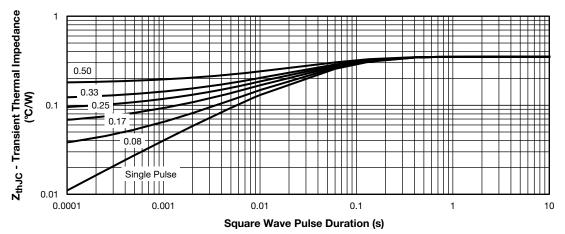


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

### **ORDERING INFORMATION TABLE**

Device code	vs-	50	Т	Р	S	12	A	L	-М3

1 - Vishay Semiconductors product

2 - Current code (50 = 50 A)

3 - Circuit configuration:

T = thyristor

P = TO-247AD 3L package

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage code (12 = 1200 V)

7 - A = Low I<sub>GT</sub> selection

8 - Package L = long lead

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

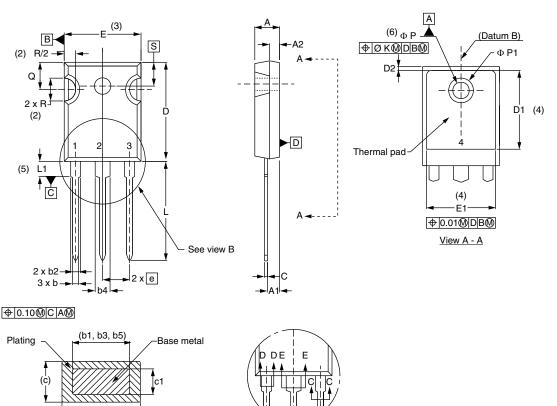
ORDERING INFORMATION (example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-50TPS12AL-M3	25	500	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				



### **TO-247AD 3L**

### **DIMENSIONS** in millimeters and inches



View B

0)/14001	MILLIN	IETERS	INC	HES	NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

Section C - C, D - D, E - E

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØΚ	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		
		•	•		

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4



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